

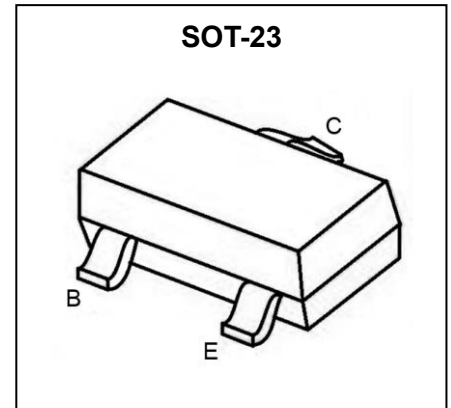


MMBT5401 Transistor(PNP)

Feature

- Small Surface Mount Package

Marking: 2L



MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	-160	V
Collector-Emitter Voltage	V _{CE0}	-150	V
Emitter-Base Voltage	V _{EB0}	-5	V
Collector Current -Continuous	I _c	-0.6	A
Power Dissipation	P _d	0.625	W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{STG}	-55~ +150	°C

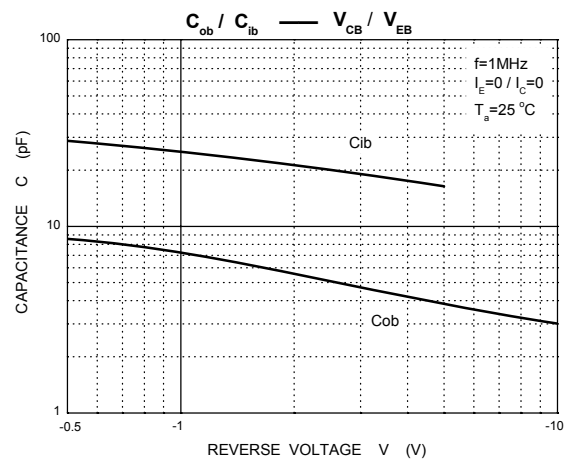
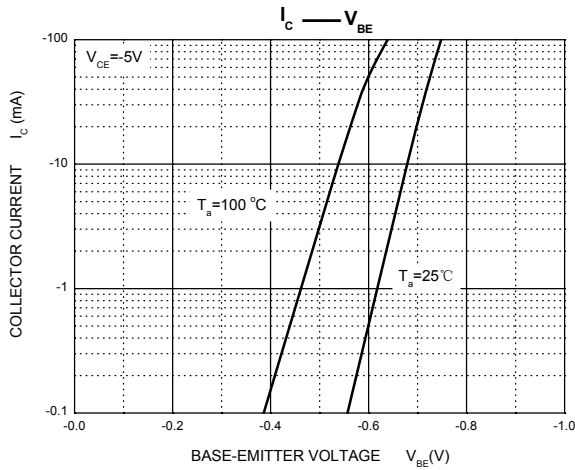
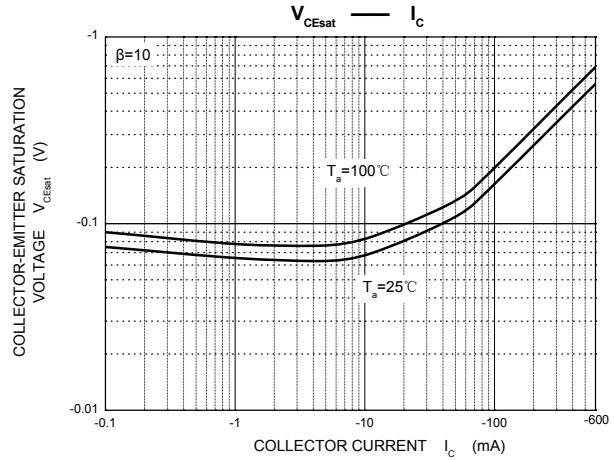
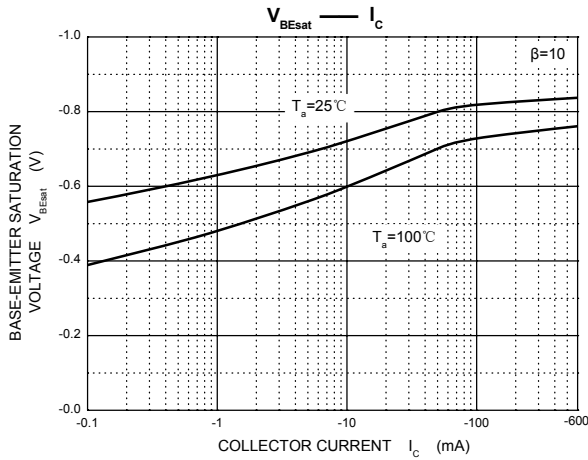
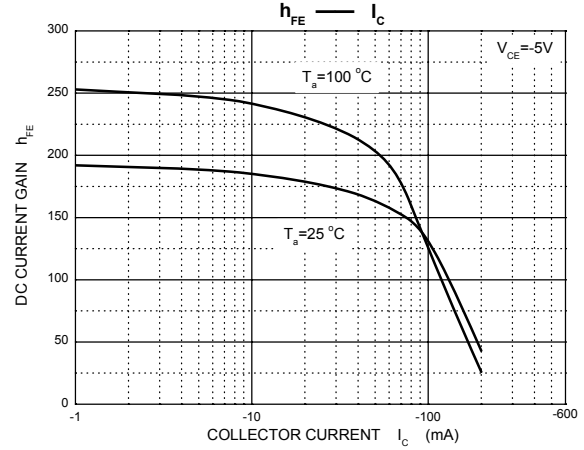
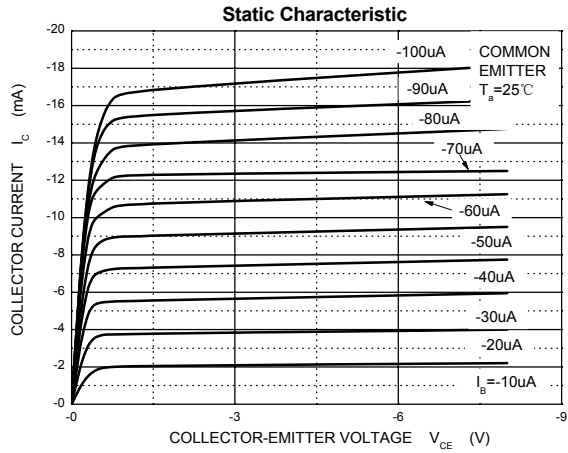
ELECTRICAL CHARACTERISTICS(T_a=25°C unless otherwise noted)

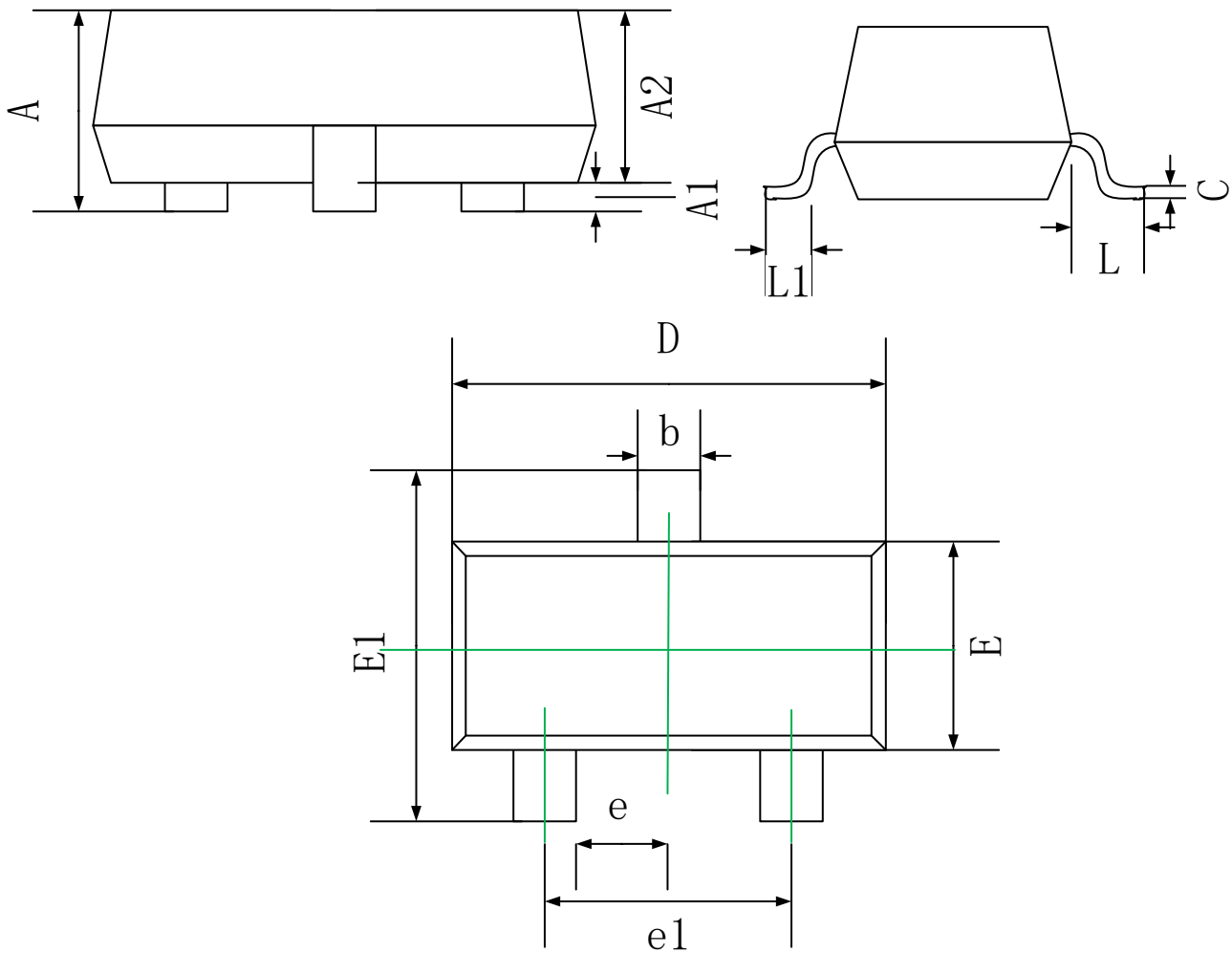
Parameter	Symbol	Test Condition	Min	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100μA, I _E =0	-160		V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-100μA, I _B =0	-150		V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-100μA, I _C =0	-5		V
Collector cut-off current	I _{CBO}	V _{CB} =-140V, I _E =0		-0.1	μA
Collector cut-off current	I _{CEO}	V _{CE} =-120V, I _B =0		-0.1	μA
Emitter-base cut-off current	I _{EBO}	V _{EB} =-4V, I _C =0		-0.1	μA
DC current gain	h _{FE}	V _{CE} =-5V, I _C =-1mA	80		
		V _{CE} =-5V, I _C =-10mA	100	300	
		V _{CE} =-5V, I _C =-50mA	50		
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-10mA, I _B =-1mA		-0.2	V
		I _C =-50mA, I _B =-5mA		-0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-10mA, I _B =-1mA		-1	V
		I _C =-50mA, I _B =-5mA		-1	V
Transition frequency	f _T	V _{CE} = -5V, I _C =-10mA, f =30MHZ	100		MHZ

CLASSIFICATION OF h_{FE}

RANK	L	H
RANGE	100-200	200-300

Typical Characteristics



SOT-23 Package Information


Symbol	Dimensions In Millimeters	
	Min.	Max.
A	0.90	1.40
A1	0.00	0.10
A2	0.90	1.30
b	0.30	0.50
c	0.08	0.19
D	2.70	3.10
E	1.20	1.65
E1	2.20	3.00
e	0.95 REF.	
e1	1.78	2.04
L	0.55 REF.	
L1	0.20	0.50